

12-03-01

MEMC 99-0900 (2632) PATENT #8/B La 12/10/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Fuerhoff et al. Serial No. 09/502,340 Filed February 10, 2000 Art Unit 1765

For METHOD AND APPARATUS FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS

Examiner M. Anderson

October 31, 2001

AMENDMENT_A

RECEIVED
TC 1700

TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action mailed July 31, 2001, please enter the following amendments:

IN THE TITLE

Please replace the Title of the application with the following:

--METHOD OF CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS--.

IN THE CLAIMS

Please amend claim 2 as follows:

2. The method of claim 1 wherein the step of adjusting the power includes applying a pulse of power to the heater, said power pulse having an amplitude greater than a steady state value corresponding directly to the temperature set point.

Please cancel claims 11-18 without prejudice to their patentability.